## NSN 5961-01-103-5965

Semiconductor Device Set - Page 1 of 2



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Inclosure Material:
Metal all transistor
Overall Length:
0.240 inches all transistor and 0.260 inches all transistor
Terminal Length:
0.500 inches all transistor
Overall Diameter:
0.350 inches all transistor and 0.370 inches all transistor
Internal Configuration:
Junction contact all transistor
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-39 all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
2 transistor
Mounting Method:
Terminal all transistor
Terminal Circle Diameter:
0.190 inches all transistor
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
40.0 breakdown voltage, collector-to-emitter, base open all transistor
Current Rating Per Characteristic:
800.00 milliamperes source cutoff current all transistor
Power Rating Per Characteristic:
800.0 milliwatts small-signal input power, common-collector absolute all transistor
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction all transistor
Terminal Type And Quantity:
3 uninsulated wire lead all transistor
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:

No

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Semiconductor Device Set - Page 2 of 2



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